
Lecture8:

Diode models and circuits (2)

Sung-Min Hong (smhong@gist.ac.kr)

Semiconductor Device Simulation Lab.
School of Information and Communications
Gwangju Institute of Science and Technology

A simple math, again

- Taylor series expansion
 - Consider a function, $f(x)$.
 - Then, at $x_0 + \Delta x$ (Δx is small.), the function value would be similar to that at x_0 :

$$f(x_0 + \Delta x) \approx f(x_0)$$

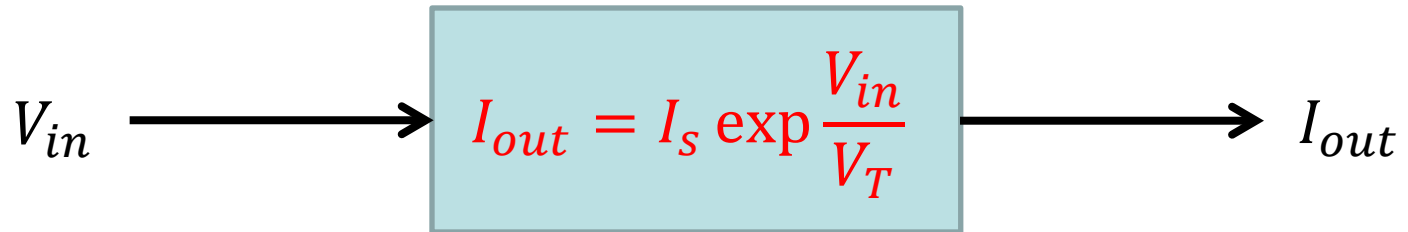
- A better approximation?

$$f(x_0 + \Delta x) \approx f(x_0) + \left. \frac{df(x)}{dx} \right|_{x=x_0} \Delta x$$

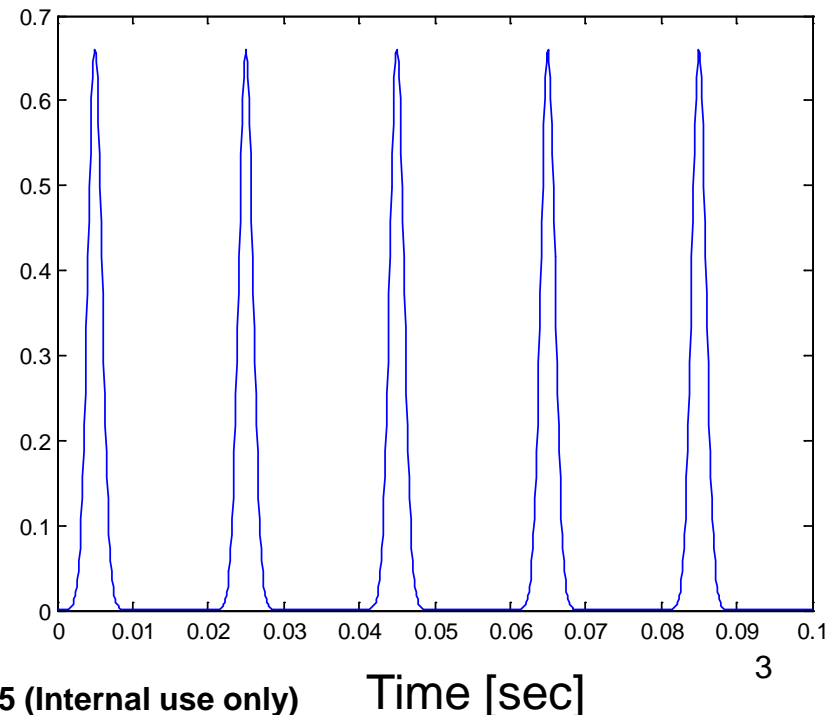
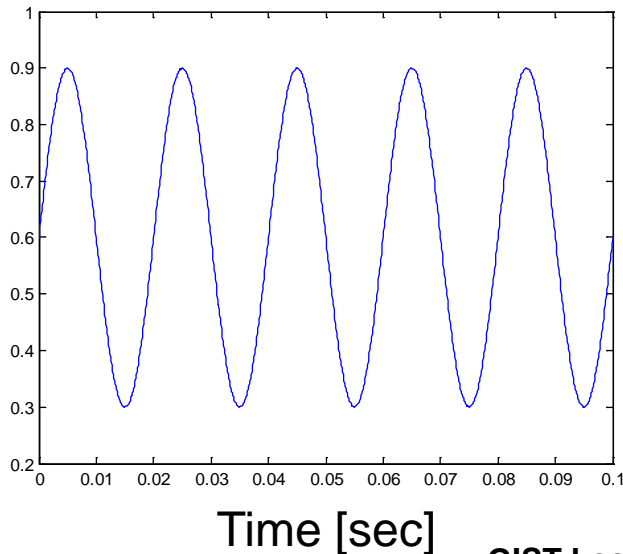
- Nonlinear function → linearly approximated!

A system

- A system (You know what it actually represents.)

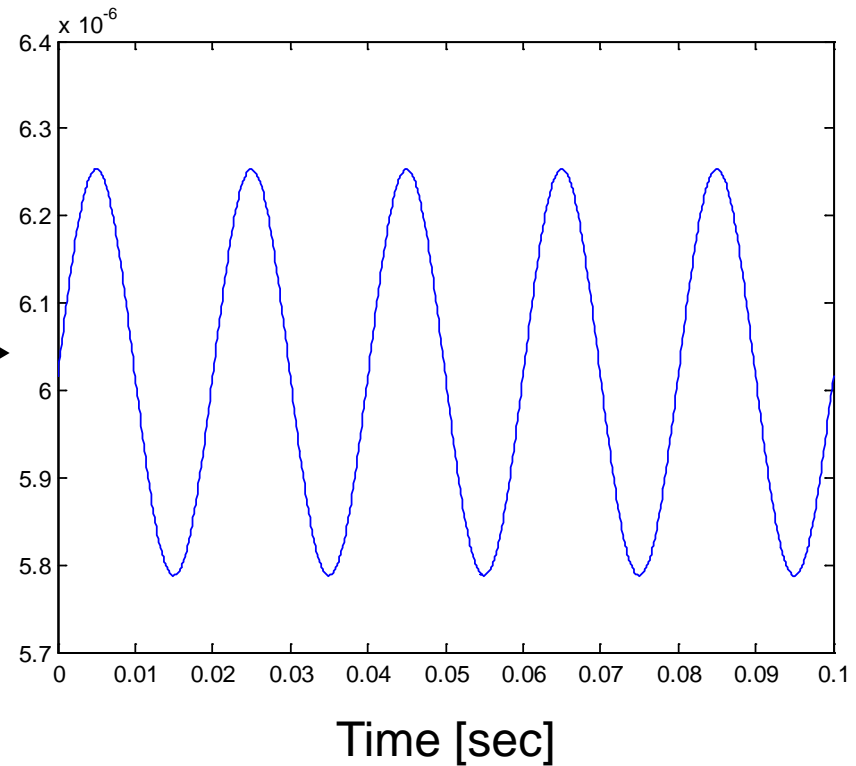
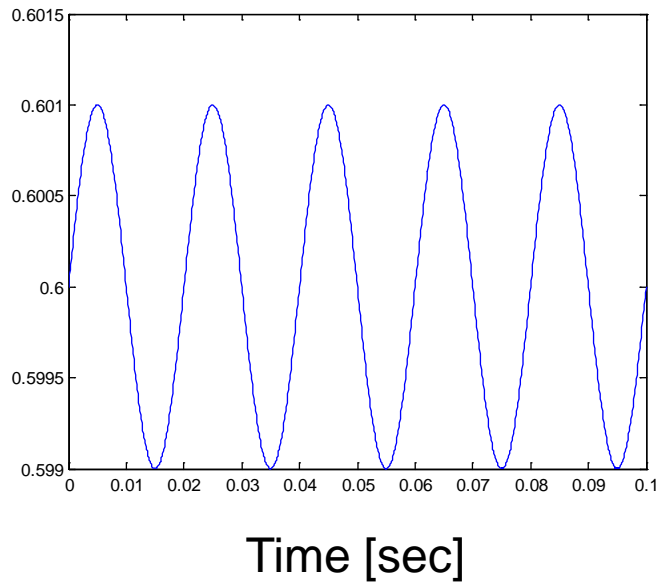


- When $V_{in} = 0.6 + 0.3 \sin 2\pi f t$,
 - Certainly, nonlinear!



Smaller amplitude?

- When $V_{in} = 0.6 + 0.001 \sin 2\pi f t$,
 - Nonlinear?



Verbatim (p. 66)

- These thought lead us to the extremely important concept of “small-signal operation,” whereby the circuit experiences only small changes in voltages and currents.
- Therefore it can be simplified through the use of “small-signal models” for nonlinear devices.
- The simplicity arises because such models are linear, allowing standard circuit analysis and obviating the need for iteration.

Exponential

- Simple, but important example

- A diode is biased to a voltage V_{D1} .

- The current is given by I_{D1} .

$$I_{D2} = I_s \exp \frac{V_{D1} + \Delta V}{V_T} = I_s \exp \frac{V_{D1}}{V_T} \exp \frac{\Delta V}{V_T}$$

$$I_{D2} \approx I_{D1} \left(1 + \frac{\Delta V}{V_T} \right)$$

Example 3.18

- A diode is biased at a current of 1 mA.
 - Determine the current change if V_D changes by 1 mV.

$$\Delta I_D = \frac{I_D}{V_T} \Delta V_D \approx 40 \mu\text{A}$$

- Small-signal resistance
 - As far as small changes in the diode current and voltage are concerned, the device behaves as a linear resistor.

$$r_d = \frac{V_T}{I_D}$$

Example 3.19

- When the small change in the diode voltage is time-varying,
 - What happens?

$$I_{D2} = I_s \exp \frac{V_{D1} + \Delta V}{V_T} = I_s \exp \frac{V_{D1}}{V_T} \exp \frac{\Delta V}{V_T}$$

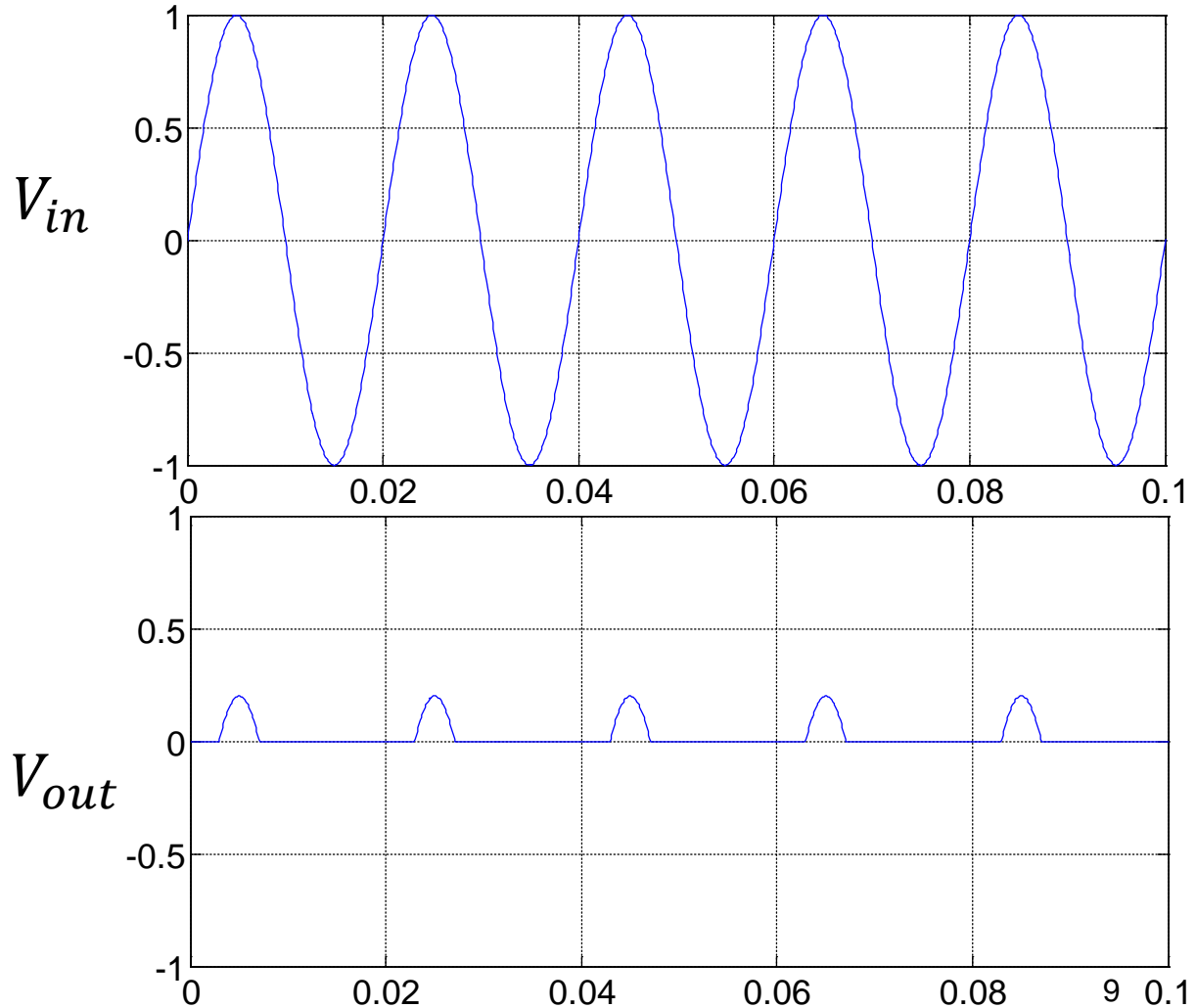
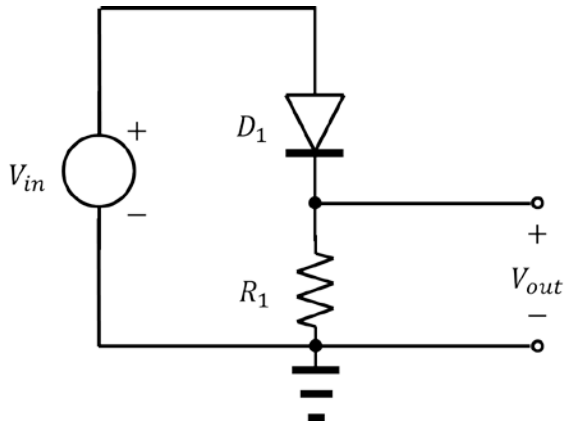
$$I_{D2} \approx I_{D1} \left(1 + \frac{\Delta V}{V_T} \right)$$

$$I_{D2} = I_s \exp \frac{V_{D1} + \Delta V \cos \omega t}{V_T} = I_s \exp \frac{V_{D1}}{V_T} \exp \frac{\Delta V \cos \omega t}{V_T}$$

$$I_{D2} \approx I_{D1} \left(1 + \frac{\Delta V \cos \omega t}{V_T} \right)$$

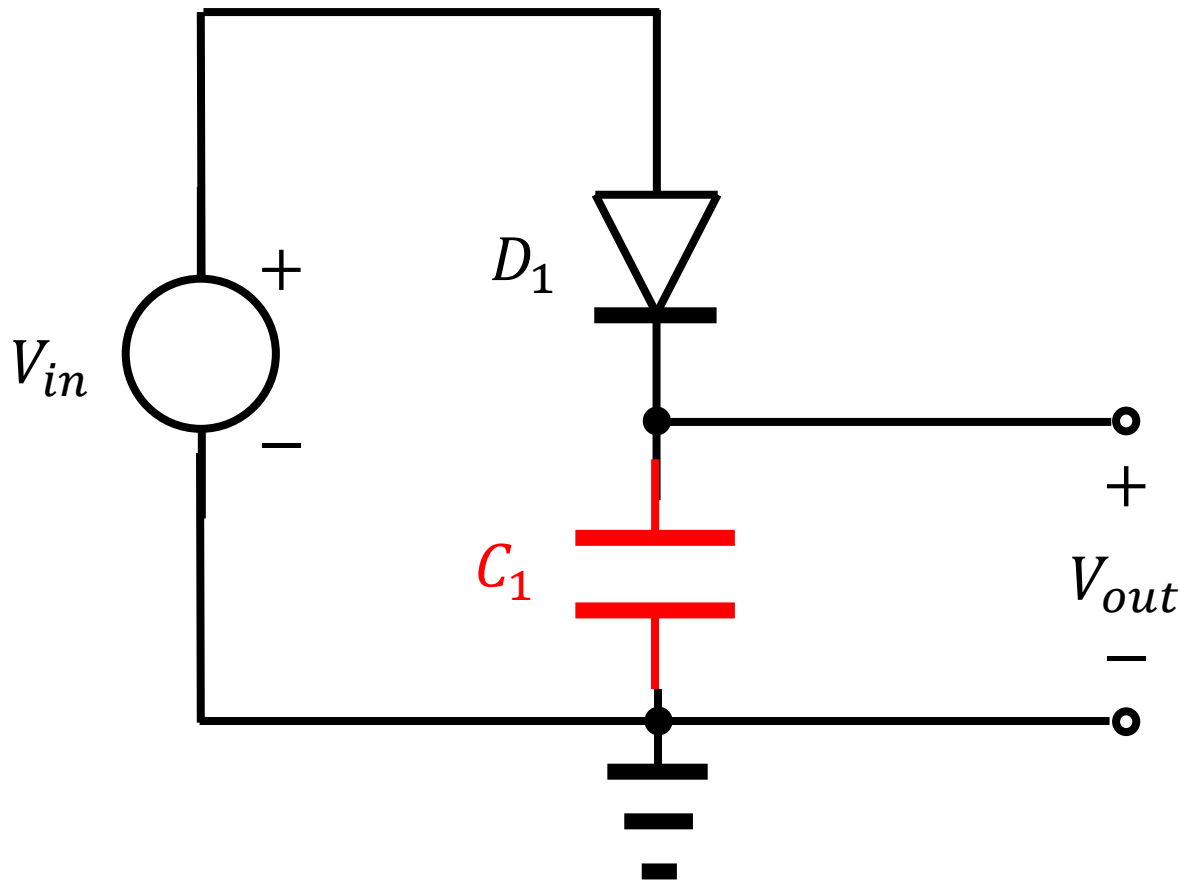
Rectifier, revisited

- Constant-voltage model?



Introducing a capacitor

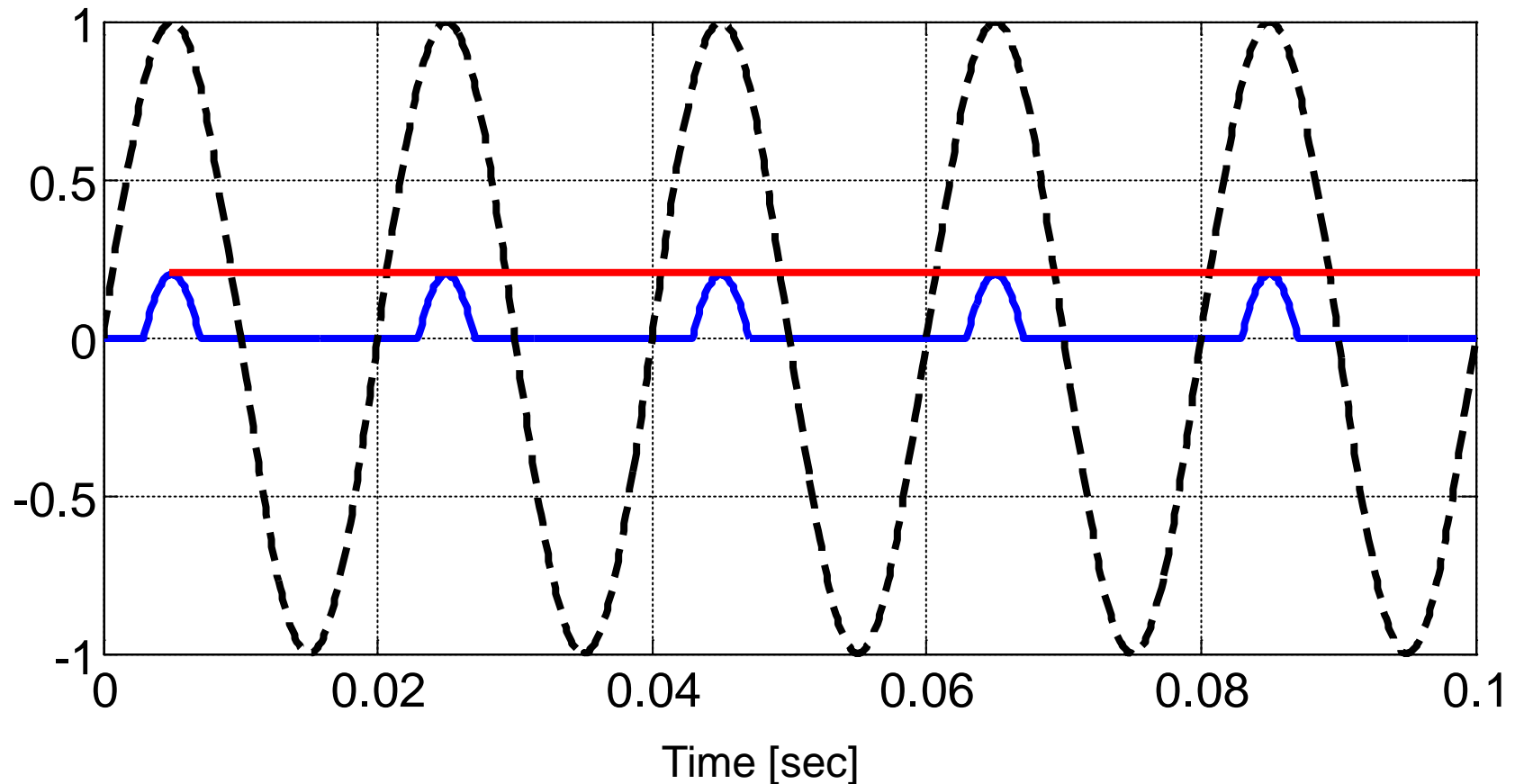
- Difference from the previous one?



Introducing a capacitor

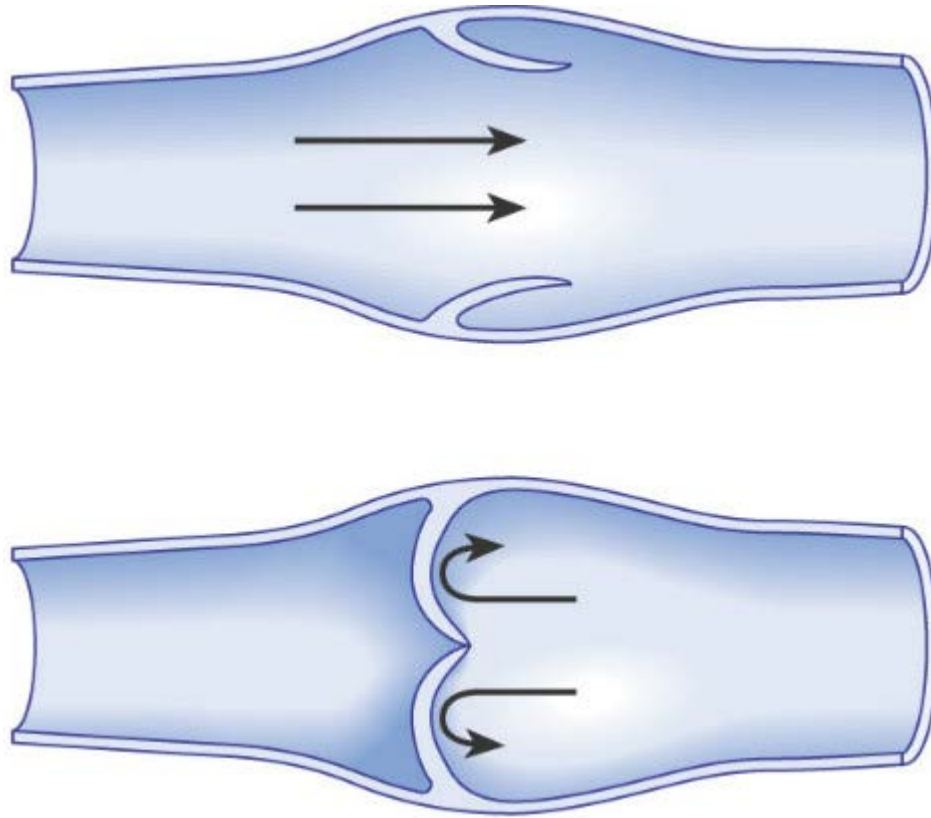
- Difference from the previous one?

Voltage [V]



Analogy

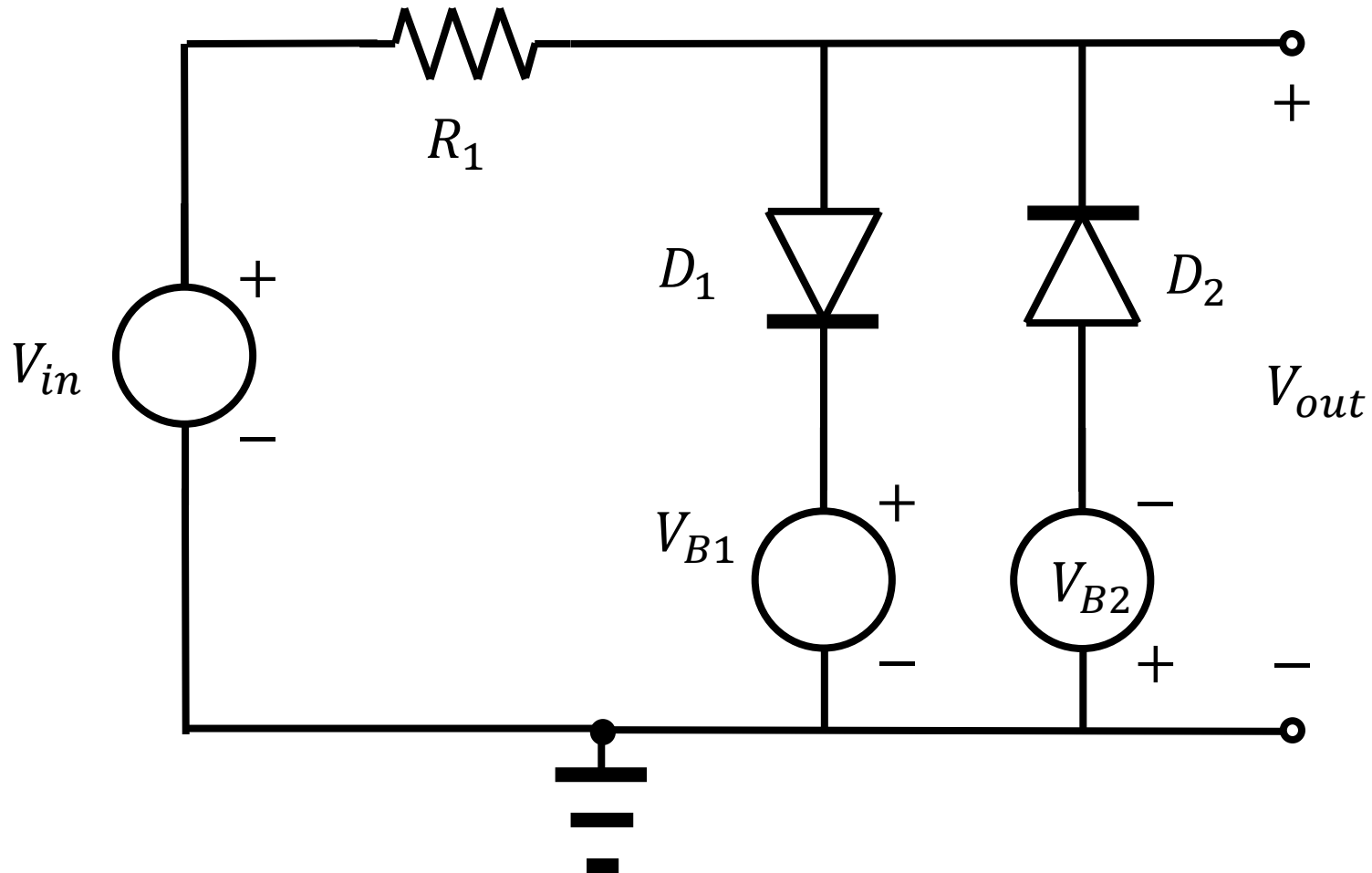
- A blood vessel



(Google image)

Limiter

- Level-shift for both half cycles



Read your textbook.

- Now we will move to the MOSFET.
 - Therefore, directly jump to Ch.6.
 - On the next Monday, the structure of the MOSFET will be discussed.
 - Sec. 6.1.
- *Interested?*
 - *Search it in the internet.*